ESD Protection Diode Array

Dual Common Anode

These dual monolithic silicon surge protection diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SOT–23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range 5.0 V to 36 V
- Peak Power 300 Watt (8/20 μs)
- Low Leakage 1.0 μA
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics:

CASE: Void-Free, Transfer-Molded, Thermosetting Plastic Case

FINISH: Corrosion Resistant Finish, Easily Solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

Package Designed for Optimal Automated Board Assembly Small Package Size for High Density Applications Available in 8 mm Tape and Reel

Use the Device Number to Order the 7 Inch/3,000 Unit Reel Replace the "T1" with "T3" in the Device Number to Order the 13 Inch/10,000 Unit Reel



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SOT-23 CASE 318 STYLE 12

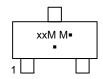


PIN 1. CATHODE

2. CATHODE

ANODE

MARKING DIAGRAM



xxM = Device Code

xx = 05, 12, 15, 24, 36

M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
SM05T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SZSM05T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM12T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM15T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM24T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM36T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 20 μs (Note 1) @ T _L ≤ 25°C	P _{pk}	300	W
IEC 61000-4-2 (ESD) Air Contact		±15 ±26	kV
IEC 61000-4-4 (EFT)		40	А
IEC 61000-4-5 (Lightning)		12	Α
Total Power Dissipation on FR–5 Board (Note 2) @ T _A = 25°C Derate above 25°C Thermal Resistance, Junction–to–Ambient	P _D R _{θJA}	225 1.8 556	mW mW/°C °C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ T _A = 25°C Derate above 25°C Thermal Resistance, Junction–to–Ambient	P _D R _{θJA}	300 2.4 417	mW mW/°C °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	– 55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

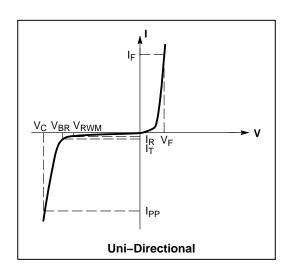
- 1. Non-repetitive current pulse per Figure 3
- 2. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.
- 3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

NOTE: Other voltages may be available upon request

ELECTRICAL CHARACTERISTICS

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ IPP
V_{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V _{BR}
I _F	Forward Current
V _F	Forward Voltage @ I _F
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}
I _{ZK}	Reverse Current
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

				V _{BR} , Breakd	own Voltage		V _C @	Max I _{PP}	Typical Capacitance
		V _{RWM}	I _R @ V _{RWM}	(Vo	lts)	Ι _Τ	1 Amp	(Note 4)	(pF)
Device*	Device Marking	(Volts)	(μΑ)	Min	Max	mA	(Volts)	(Amps)	Pin 1 to 3 @ 0 Volts
SM05T1G	05M	5	10	6.2	7.3	1.0	9.8	17	225
SM12T1G	12M	12	1.0	13.3	15.75	1.0	19	12	95
SM15T1G	15M	15	1.0	16.7	19.6	1.0	24	10	100
SM24T1G	24M	24	1.0	26.7	31.35	1.0	43	5.0	60
SM36T1G	36M	36	1.0	40.0	46.95	1.0	60	4.0	45

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{4. 8/20} μs pulse waveform per Figure 3

^{*}Include SZ-prefix devices where applicable.

TYPICAL CHARACTERISTICS

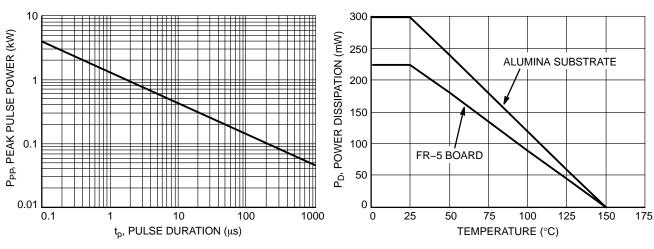


Figure 1. Non-Repetitive Peak Pulse Power versus Pulse Time

Figure 2. Steady State Power Derating Curve

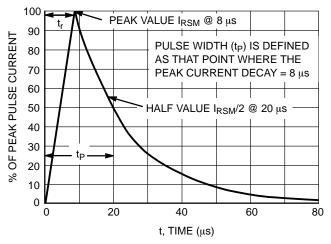


Figure 3. 8/20 μs Pulse Waveform

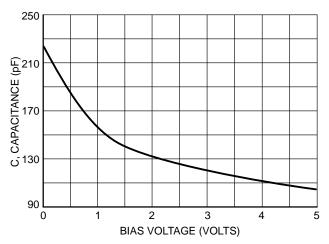


Figure 4. Typical Diode Capacitance (SM05)

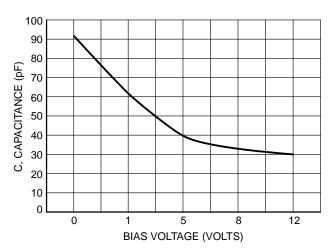


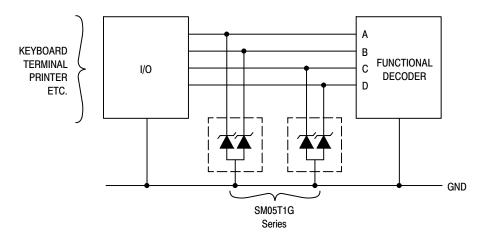
Figure 5. Typical Diode Capacitance (SM12)

TYPICAL COMMON ANODE APPLICATIONS

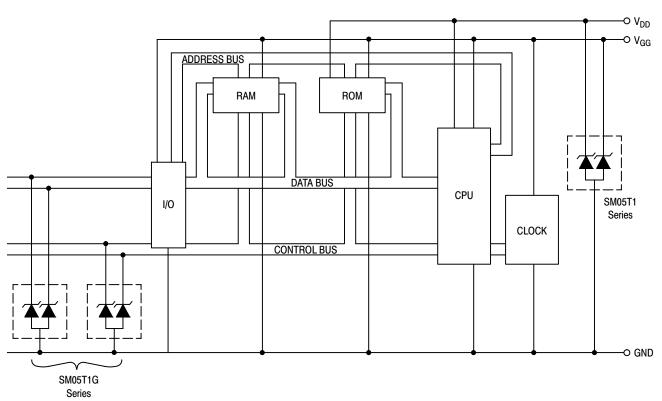
A quad junction common anode design in a SOT-23 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of surge protection applications are illustrated below.

Computer Interface Protection



Microprocessor Protection



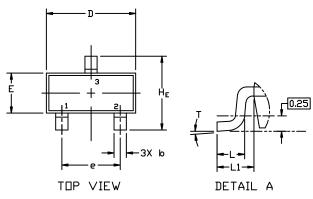


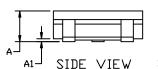


SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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